

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	1222	257/776	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 17:55
L5	201	257/653	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 17:55
S1	1866	(impurity adj density) with region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:39
S2	1866	(impurity adj density) with region with region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:40
S3	2	(impurity adj density) with region with plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:40
S4	5	(impurity adj density) with plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:41
S5	92	(polysilicon adj plug):clm. with (insulating or dielectric).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:42
S7	77	(second adj insulating adj (layer or film)) same (polysilicon adj plug) same (opening or hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:43
S8	1	10/760503	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:43

## EAST Search History

S9	52	(first adj insulating adj (film or layer)) same (second adj insulating adj (layer or film)) same (polysilicon adj plug) same (opening or hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:45
S10	11	((first adj insulating adj (film or layer)) same (second adj insulating adj (layer or film)) same (polysilicon adj plug) same (opening or hole)):clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:44
S11	0	(first adj insulating adj (film or layer)) same (second adj insulating adj (layer or film)) same (polysilicon adj plug) same (opening or hole) and (pn near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:45
S12	0	((first adj insulating adj (film or layer)) same (second adj insulating adj (layer or film)) same (polysilicon adj plug) same (opening or hole)) and (pn near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:45
S13	0	((first adj insulating adj (film or layer)) same (polysilicon adj plug) same (opening or hole)) and (pn near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:45
S14	3	((first adj insulating adj (film or layer)) and (polysilicon adj plug) same (opening or hole)) and (pn near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:45
S15	6	((first adj insulating adj (film or layer)) and (polysilicon adj plug) and (opening or hole)) and (pn near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:46
S16	64	((insulating adj (film or layer)) and (polysilicon adj plug) and (opening or hole)) and (pn near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:46
S17	73	(((dielectric or insulating) adj (film or layer)) and (polysilicon adj plug) and (opening or hole)) and (pn near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 22:47

## EAST Search History

S18	8	(((dielectric or insulating) adj (film or layer)) and (polysilicon adj plug) and (opening or hole)) and (pn near junction adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 23:00
S19	3	(((dielectric or insulating) adj (film or layer)) same (polysilicon adj plug)).clm. and (pn near junction adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 23:02

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	15	(first near2 polysilicon near2 plug) same semiconductor same surface same (second near2 polysilicon near2 plug)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:06
L2	3	(polysilicon near2 plug) same ((impurity or diffusion) near2 region) same pn near junction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:07
L3	3	"5386138"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:08
L4	4	(region same (polysilicon near2 plug) same substrate same surface same (pn near junction))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:11
L5	1	fukuro and oki	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:11
L6	1	fukuro and taketo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:12
L7	0	(polysilico near2 plug)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:12
L8	3496	(polysilicon near2 plug)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:12
L9	62	(polysilicon near2 plug) same (diode or ((pn or p/n or p-n) near junction))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:25

## EAST Search History

L10	50	(polysilicon near2 plug) same (diode or ((pn or p/n or p-n) near junction) same substrate same surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:15
L11	49	(polysilicon near2 plug) same (diode or ((pn or p/n or p-n) near junction) same substrate same surface same (wiring or interconnector))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:16
L12	4	(polysilicon near2 plug) same (diode or ((pn or p/n or p-n) near junction)) same substrate same surface same (wiring or interconnector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:19
L14	27	(polysilicon near2 plug) same (diode or ((pn or p/n or p-n) near junction)) same (wire or wiring or interconnect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:26
L15	2	(polysilicon near2 plug) same (diode or ((pn or p/n or p-n) near junction)) same (wire or wiring or interconnect) same (dope or doping or doped or dopant or concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:27
L16	2	(polysilicon near2 plug) same (diode or ((pn or p/n or p-n) near junction)) same (wire or wiring or interconnect) same (dope or doping or doped or dopant or concentration or density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:27
L17	5	(polysilicon near2 plug) same (diode or ((pn or p/n or p-n) near junction)) same (wire or wiring or interconnect) same (dope or doping or doped or dopant or concentration or density or impurity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:27
L18	27	(polysilicon near2 plug) same (diode or ((pn or p/n or p-n) near junction)) same (wire or wiring or interconnect) and (dope or doping or doped or dopant or concentration or density or impurity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:30

## EAST Search History

L19	22	I18 and ((polysilicon near2 plug) near10 (dope or doping or doped or dopant or concentration or densiry or impurity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:34
L20	0	I18 and ((polysilicon near2 plug) near10 (dope or doping or doped or dopant or concentration or densiry or impurity)) and "cm.sup.-2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:33
L21	0	I18 and ((polysilicon near2 plug) near10 (dope or doping or doped or dopant or concentration or densiry or impurity)) and "cm.sup.-2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:35
L22	22	I18 and ((polysilicon near2 plug) near10 (dope or doping or doped or dopant or concentration or densiry or impurity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 10:57
L23	6	(polysilicon near2 plug) same (insulating or dielectric or oxide or insulationg) same (diffusion or source or drain or source/drain or impurity) same ((pn or p/n or p-n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:03
L24	844	(polysilicon near2 plug) same substrate same (diffusion or impurity or source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:04
L25	7	(polysilicon near2 plug) same substrate same (diffusion or impurity or source or drain or source/drain) same ((pn or p-n or p/n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:05
L26	35	(polysilicon near2 plug) same substrate same (diffusion or impurity or source or drain or source/drain) and ((pn or p-n or p/n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:11
L27	445	(polysilicon near plug).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:11

## EAST Search History

L28	4	(polysilicon near plug).clm. and ((pn or p/n or p-n) near junction).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:12
L29	177	(polysilicon near plug) and ((pn or p/n or p-n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:12
L30	64	((dope or doping or doped) near2 polysilicon near plug) and ((pn or p/n or p-n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:13
L31	75	((dope or doping or doped or dopant or impurity) near5 polysilicon near plug) and ((pn or p/n or p-n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:13
L32	5	(((dope or doping or doped or dopant or impurity) near5 polysilicon near plug) same (interconnect or wiring)) and ((pn or p/n or p-n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:16
L33	7	(((dope or doping or doped or dopant or impurity) near10 polysilicon near plug) same (interconnect or wiring)) and ((pn or p/n or p-n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:19
L34	39	(((dope or doping or doped or dopant or impurity) near10 polysilicon near plug) and (interconnect or wiring)) and ((pn or p/n or p-n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:20
L35	3	"5386138"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:22
L36	1383	(polysilicon near2 plug) near10 (insulating or dielectric or insulation or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:23
L37	137	(surface near2 polysilicon near2 plug) near10 (insulating or dielectric or insulation or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:29

## EAST Search History

L38	12	(surface near2 polysilicon near2 plug) near10 (insulating or dielectric or insulation or oxide) and ((polysilicon near2 plug) near10 (wire or wiring or interconnect))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:31
L39	13	(surface near2 polysilicon near2 plug) near10 (insulating or dielectric or insulation or oxide) and ((polysilicon near2 plug) with (wire or wiring or interconnect))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:31

## EAST Search History

L50	99	I49 and ((polysilicon near2 plug) near10 (dope or doping or doped or dopant or impurity or concentration or level or density))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:33
L51	10	I49 and ((polysilicon near2 plug) near10 (dope or doping or doped or dopant or impurity or concentration or level or density)) and ((polysilicon near2 plug) near10 (cover or covering or covered) near10 (insulating or dielectric or insulation or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:36
L52	19	((polysilicon near2 plug) near10 (dope or doping or doped or dopant or impurity or concentration or level or density)) and ((polysilicon near2 plug) near10 (cover or covering or covered) near10 (insulating or dielectric or insulation or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:36
L53	15	((polysilicon near2 plug) near10 (dope or doping or doped or dopant or impurity or concentration or level or density)) and ((polysilicon near2 plug) near10 (cover or covering or covered) near10 (insulating or dielectric or insulation or oxide)) and times	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:36

## EAST Search History

L64	121	I63 and (times)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:38
L65	106	I63 and ((polysilicon near2 plug) with (dope or doping or doped or dopant or concentration or level or density))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/10 11:38